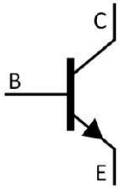


Silicon NPN transistor in a SOT-323 Plastic Package.

High h_{FE} and V_{CEO}



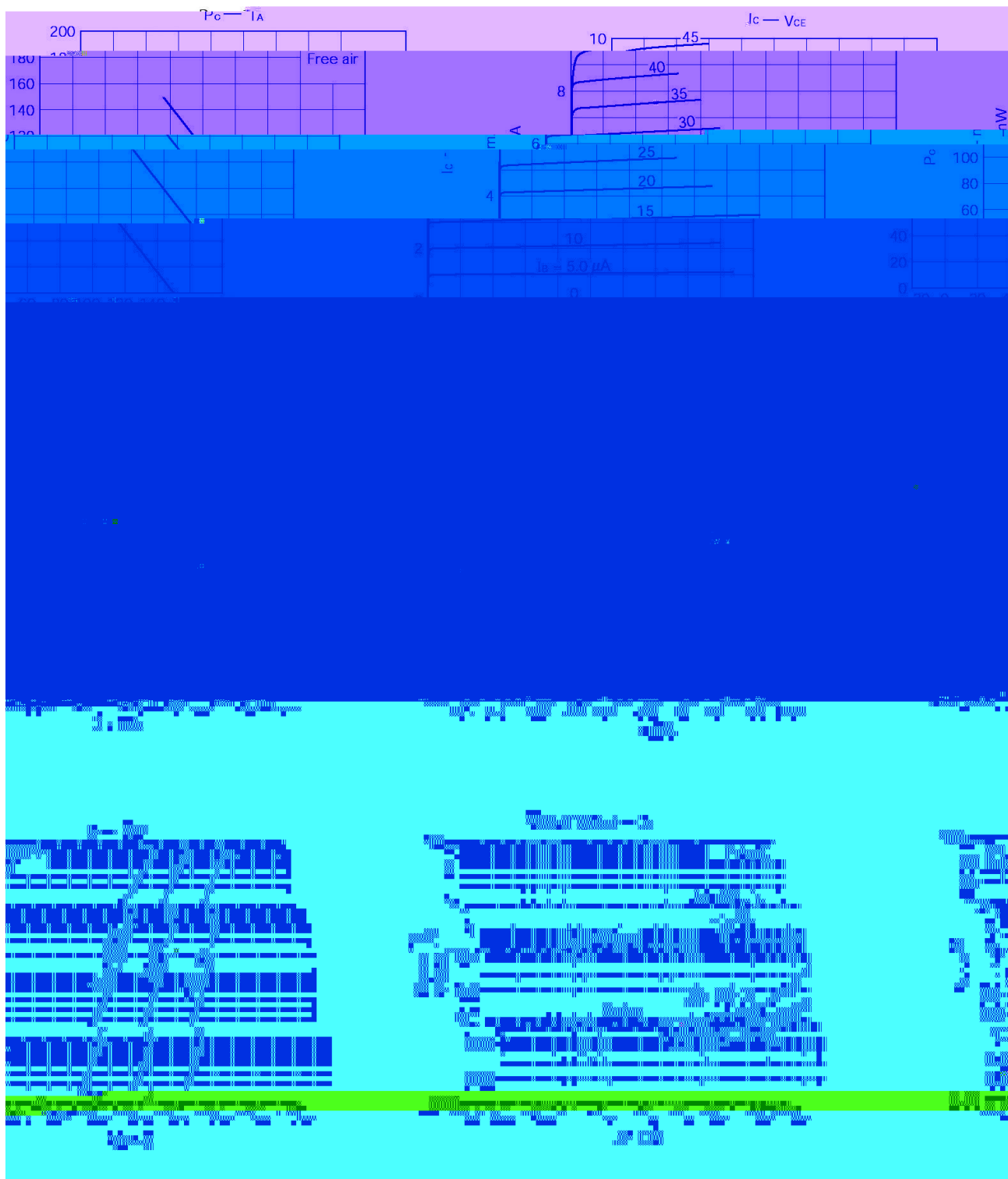

绝对最大额定值 / Absolute Maximum Ratings(Ta=25 ℃)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	60	V
Collector to Emitter Voltage	V_{CEO}	50	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	100	mA
Collector Power Dissipation	P_C	150	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

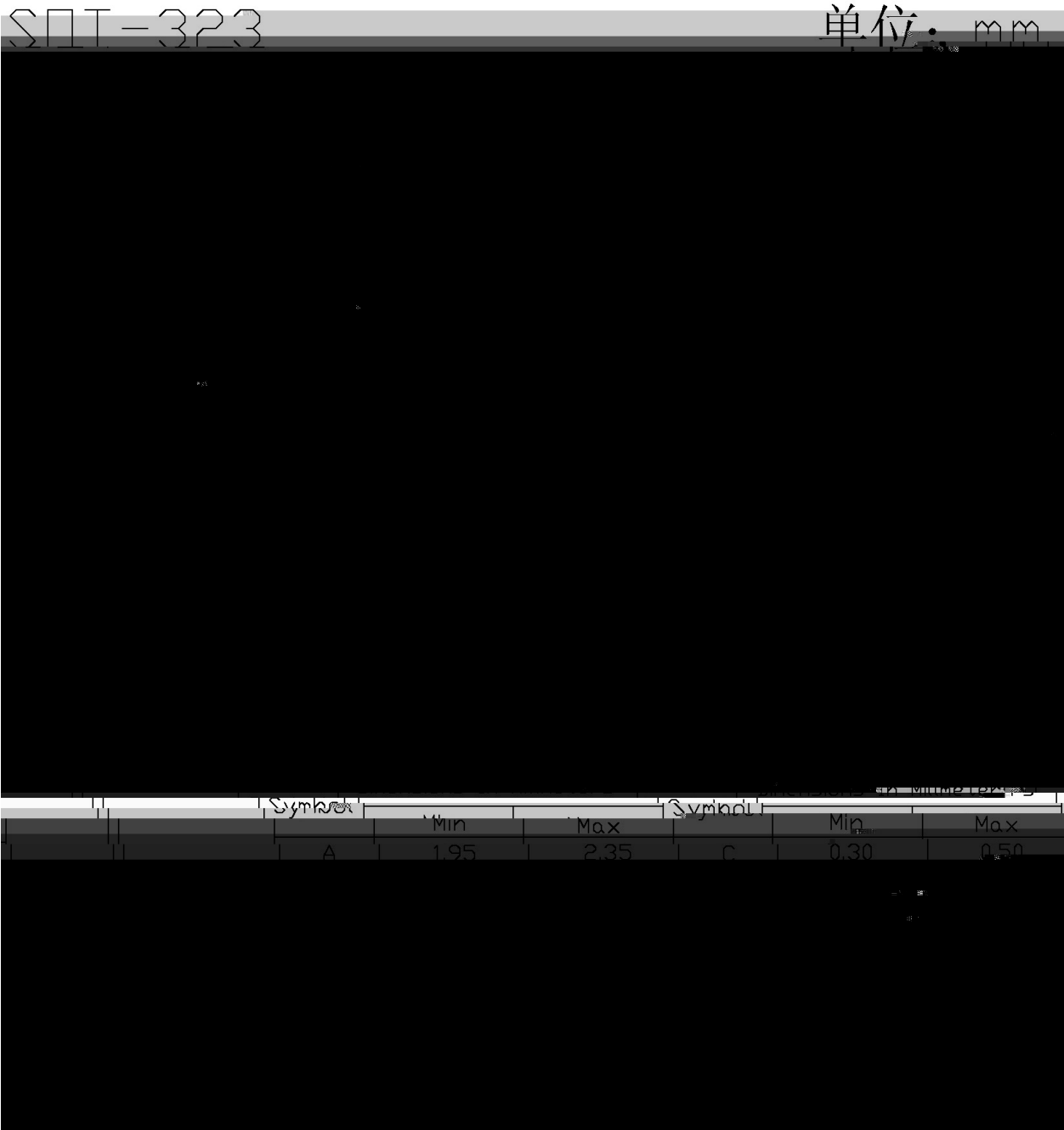
电 气 特 性 / Electrical Characteristics(Ta=25 ℃)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	$V_{CB}=60V$ $I_E=0$			0.1	μA
Emitter Base Cut-Off Current	I_{EBO}	$V_{EB}=5.0V$ $I_C=0$			0.1	μA
DC Current Gain	h_{FE}	$V_{CE}=6.0V$ $I_C=1.0mA$	90	200	600	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=100mA$ $I_B=10mA$		0.15	0.3	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=100mA$ $I_B=10mA$		0.86	1.0	V
Base to Emitter Voltage	V_{BE}	$V_{CE}=6.0V$ $I_C=1.0mA$	0.55	0.62	0.65	V
Transition Frequency	f_T	$V_{CE}=6.0V$ $I_C=10mA$		250		MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=6.0V$ $f=1.0MHz$ $I_E=0$		3.0		pF

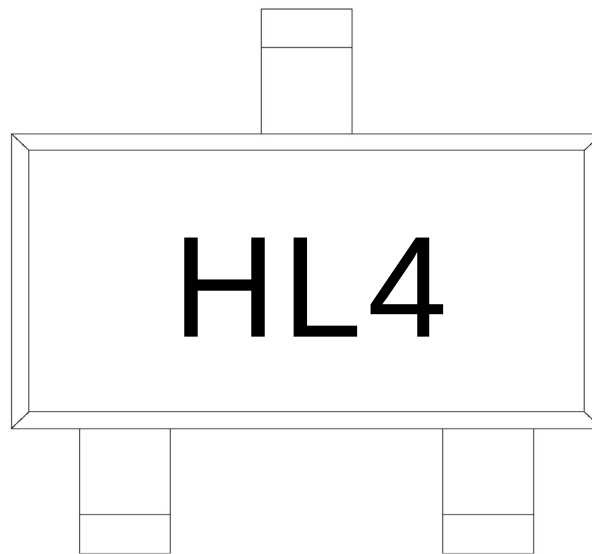
Electrical Characteristic Curve



⌘ É Ò Ì ¢ / Package Dimensions



4. 1. 1 / Marking Instructions



H

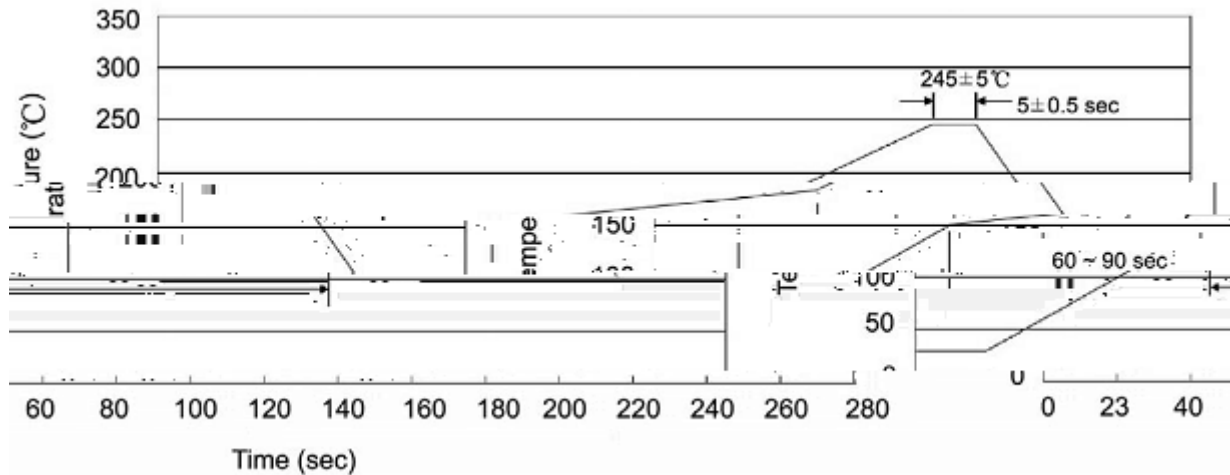
L4

Note:

H: Company Code.

L4: Product Type.

Whp shudwxuh Suriloh i ru LU Uhior z Vroghulq j+Se0l uhh,



Note:

1. Preheating: 25~150 °C, Time: 60~90 sec.
2. Peak Temp.: 245 ± 5 °C, Duration: 5 ± 0.5 sec.
3. Cooling Speed: 2~10 °C/sec.

Resistance to Soldering Heat Test Conditions

260 ± 5 °C, 10 ± 1 sec. Temp.: 260 ± 5 °C Time: 10 ± 1 sec

Packaging SPEC.

/ REEL

Package Type	Units					Dimension (unit mm ³)		
	Units/Reel	Reels/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Reel	Inner Box	Outer Box
SOT-323	3,000	10	30,000	6	180,000	7 × 8	180×120×180	390×385×205

Notices